

Sub B1
A2

1. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first insulating film formed over said insulating surface, said semiconductor layer, said gate insulating film and said gate electrode;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a pixel electrode formed over said second insulating film.

7. (Amended) A semiconductor device of claim 1 wherein a portion of said pixel electrode is located under said electrode.

A3
Sub B2

8. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film formed on said semiconductor layer;
a gate electrode formed on said gate insulating film;
a first insulating film formed over said insulating surface, said semiconductor layer, said gate insulating film and said gate electrode;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a pixel electrode formed over said second insulating film.

A4

14. (Amended) A semiconductor device of claim 8 wherein a portion of said pixel electrode is located under said electrode.

15. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first insulating film formed over said insulating surface, said semiconductor layer, said gate insulating film and said gate electrode;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a transparent pixel electrode formed over said second insulating film.

21. (Amended) A semiconductor device of claim 15 wherein a portion of said pixel electrode is located under said electrode.

23. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film formed on said semiconductor layer;
a gate electrode formed on said gate insulating film;
a first insulating film formed over said insulating surface, said semiconductor layer, said gate insulating film and said gate electrode;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a transparent pixel electrode formed over said second insulating film.

29. (Amended) A semiconductor device of claim 23 wherein a portion of said pixel electrode is located under said electrode.

30. (Amended) A semiconductor device of claim 23 wherein said transparent pixel electrode comprises indium tin oxide.

Sub B5
A7
Cm d.

31. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first insulating film formed over said insulating surface, said semiconductor layer, said gate insulating film and said gate electrode;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions wherein said electrode has a laminate structure including a first conductive film comprising aluminum and a second conductive film comprising a different material from said first conductive film;
a pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and
a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions.

Sub B6
A6

36. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first insulating film formed over said insulating surface, said semiconductor layer, said gate insulating film and said gate electrode;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions wherein said electrode has a laminate structure including a first

conductive film comprising aluminum and a second conductive film comprising a different material from said first conductive film;

AG mid. a transparent pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and

a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions.

Sub B7 42. (Amended) A semiconductor device comprising:

AG a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;

a gate insulating film adjacent to said semiconductor layer;

a gate electrode adjacent to said gate insulating film;

AG a first insulating film formed over said insulating surface, said semiconductor layer, said gate insulating film and said gate electrode;

a second insulating film comprising an organic resin formed on said first insulating film;

an electrode formed over said second insulating film and connected to one of said first and second impurity regions wherein said electrode has a laminate structure including a first conductive film comprising aluminum and a second conductive film comprising a different material from said first conductive film;

a transparent pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and

a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions, wherein said electrode comprises a same material as said conductive layer.

✓ Please add new claims 48-52 as follows.

Sub B8 /
--48. (New) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first insulating film formed over said insulating surface, said semiconductor layer, said gate insulating film and said gate electrode;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions;
A16 a pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and
a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions,
wherein a portion of said pixel electrode is located below said electrode.

49. (New) A semiconductor device of claim 48 wherein said semiconductor layer comprises crystalline silicon.

Sub C16 /
~~50. (New) A semiconductor device of claim 48 wherein said first insulating film comprises silicon oxide.~~

51. (New) A semiconductor device of claim 48 wherein said second insulating film comprises polyimide.

52. (New) A semiconductor device of claim 48 wherein said electrode has a laminate structure including a first conductive film comprising aluminum and a second conductive film comprising titanium nitride.--